**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Low threshold voltage
- Trench MOSFET technology
- · Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- AEC-Q101 qualified

## 3. Applications

- · Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-12	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-8.2	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -8.2 A; $T_j$ = 25 °C		-	15	20	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



12 V, P-channel Trench MOSFET

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D
2	D	drain		
3	G	gate	2 5	G P
4	S	source	3 8 94	S
5	D	drain	Transparent top view	017aaa257
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PMPB15XPA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PMPB15XPA	4J

12 V, P-channel Trench MOSFET

## 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-12	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-8.2	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-5.2	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-33	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode				'	
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.9	Α
ESD maximu	um rating				'	
$V_{ESD}$	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche r	uggedness		'	'		,
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = -3.8 A; DUT in avalanche (unclamped)		-	23.9	mJ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Measured between all pins.

#### 12 V, P-channel Trench MOSFET

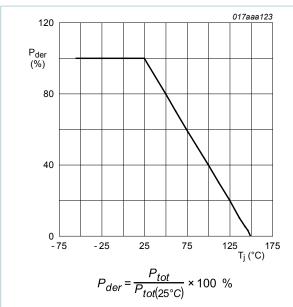


Fig. 1. Normalized total power dissipation as a function of junction temperature

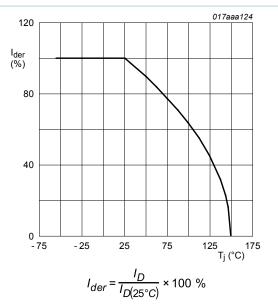
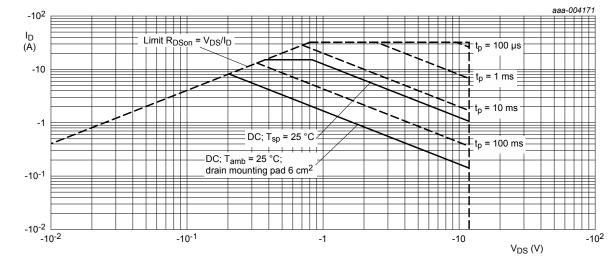


Fig. 2. Normalized continuous drain current as a function of junction temperature



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

4/14

12 V, P-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	-	[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

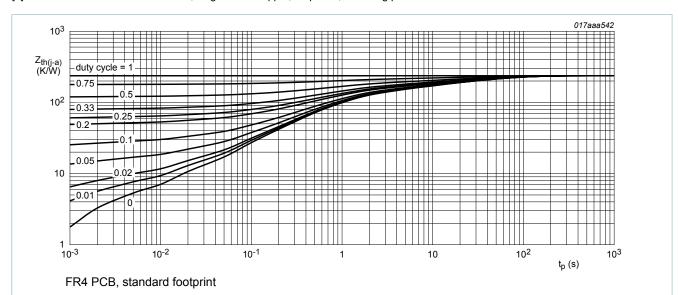


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

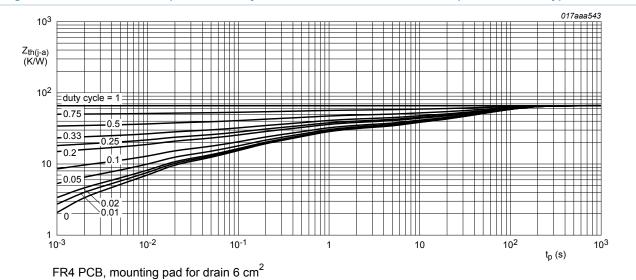


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

12 V, P-channel Trench MOSFET

### 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-12	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.4	-0.7	-1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -12 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>DS</sub> = -12 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-100	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -8.2 A; $T_j$ = 25 °C	-	15	20	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -8.2 A; $T_j$ = 150 °C	-	20	25	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -3.9 A; $T_j$ = 25 °C	-	17	23	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -3.9 A; $T_j$ = 25 °C	-	21	38	mΩ
9fs	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -8.2 A; $T_{j}$ = 25 °C	-	40	-	S
Dynamic cl	naracteristics					,
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -6 \text{ V}; I_D = -8.2 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	67	100	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	5.5	-	nC
$Q_{GD}$	gate-drain charge		-	7.3	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -6 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	2875	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	570	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	530	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -6 V; $I_{D}$ = -8.2 A; $V_{GS}$ = -4.5 V;	-	18	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	90	-	ns
$t_{d(off)}$	turn-off delay time		-	85	-	ns
t <sub>f</sub>	fall time		-	57	-	ns
Source-dra	in diode		1	,		
$V_{SD}$	source-drain voltage	$I_S = -1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.6	-1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = -1.9 \text{ A}$ ; $dI_S/dt = 100 \text{ A/µs}$ ;	_	42	_	ns
۲r	rovoros rosovory unio	$V_{GS} = 0 \text{ V}; V_{DS} = -10 \text{ V}; T_i = 25 \text{ °C}$				_

#### 12 V, P-channel Trench MOSFET

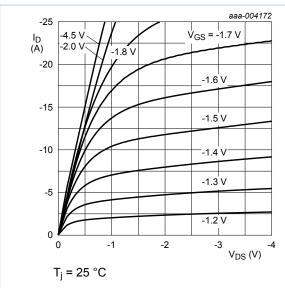


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

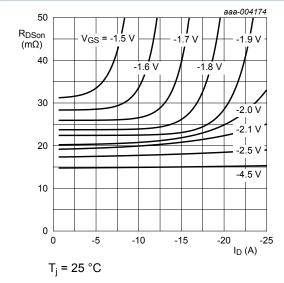


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

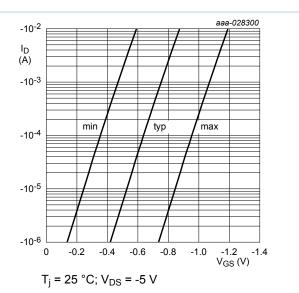


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

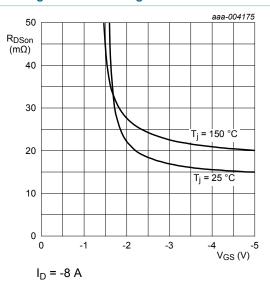


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 12 V, P-channel Trench MOSFET

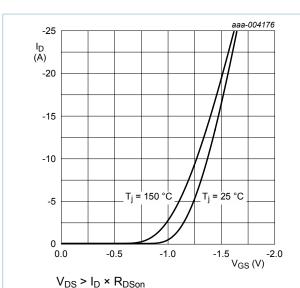


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

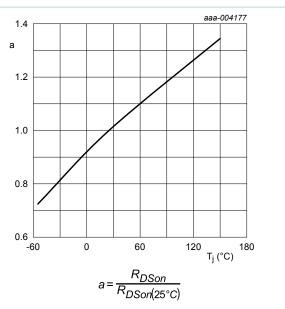


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

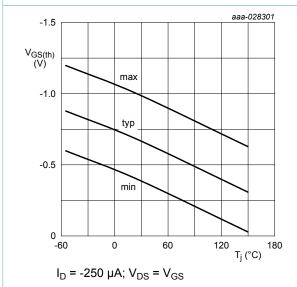


Fig. 12. Gate-source threshold voltage as a function of junction temperature

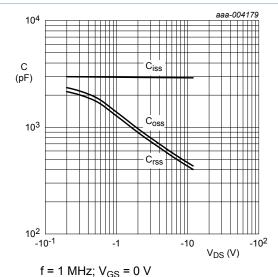


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 12 V, P-channel Trench MOSFET

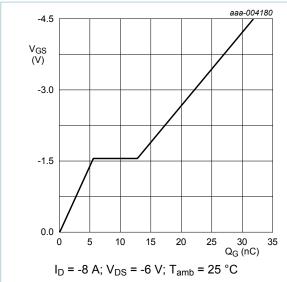


Fig. 14. Gate-source voltage as a function of gate charge; typical values

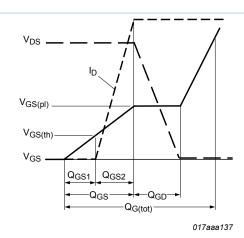


Fig. 15. Gate charge waveform definitions

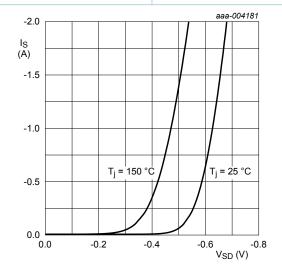
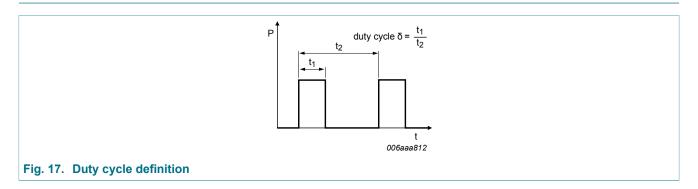


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

12 V, P-channel Trench MOSFET

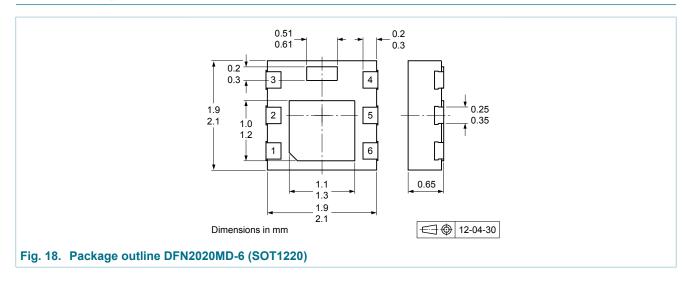
### 11. Test information



## **Quality information**

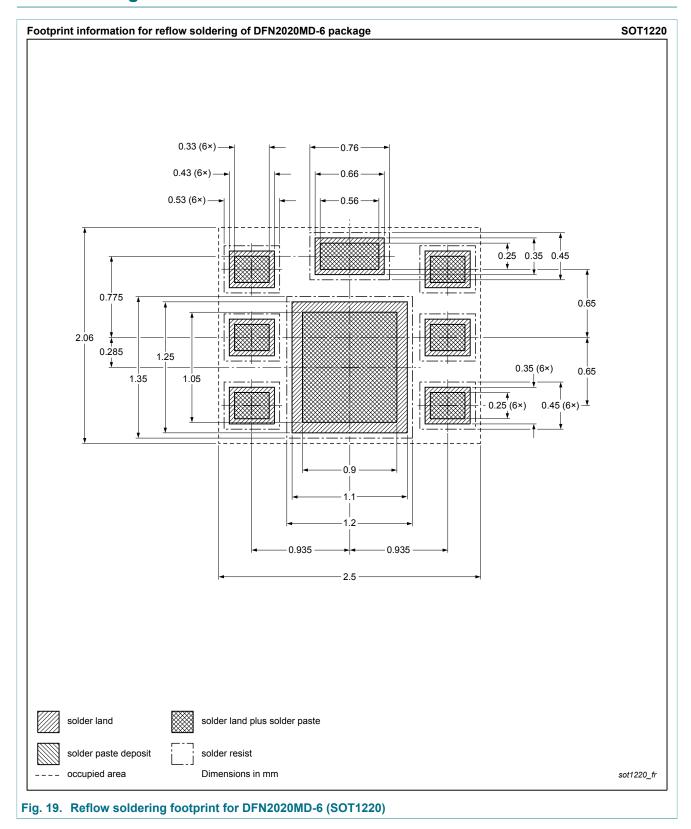
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



12 V, P-channel Trench MOSFET

## 13. Soldering



12 V, P-channel Trench MOSFET

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB15XPA v.1	20180327	Product data sheet	-	-

#### 12 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 12 V, P-channel Trench MOSFET

### 16. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	. Characteristics	€
11.	Test information	. 10
12.	. Package outline	. 10
13.	. Soldering	. 11
14.	. Revision history	.12
15.	Legal information	13

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